



#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	l <sub>D</sub> max T <sub>A</sub> = +25°C
-20V	16mΩ @ V <sub>GS</sub> = -4.5V	-9.0A
-200	22mΩ @ V <sub>GS</sub> = -2.5V	-7.7A

## **Description and Applications**

This MOSFET is designed to minimize on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for highefficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

P-CHANNEL ENHANCEMENT MODE MOSFET

#### Features and Benefits

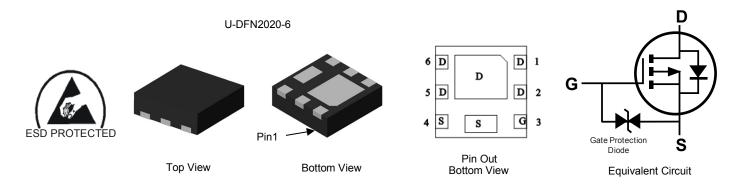
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Weight: 0.007 grams (Approximate)



#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2021UFDF-7	U-DFN2020-6	3000/Tape & Reel
DMP2021UFDF-13	U-DFN2020-6	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds..

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



## **Marking Information**

Site 1

U-DFN2020-6



P1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key	
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Suic Couc ney												
Year	201	4	2015			20	20	2021		2022	2	2023
Code	В		С			H	Η	-		J		К
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2



P1 = Product Type Marking Code YWX = Date Code Marking

Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date	Code	Kev
Daic	Ouuc	T\Cy

Year	2019	2020	2021	2022	2023	2024	2025	2026
Code	9	0	1	2	3	4	5	6
Week		1-26			27-52		53	
Code	Code			a-z			Z	
Internal Code	Sun	Mon	Τι	ue	Wed	Thu	Fri	Sat
Code	Т	U	١	V	W	Х	Y	Z



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note C) // 4.5//	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-9.0 -7.2	А
Continuous Drain Current (Note 6) $V_{GS}$ = -4.5V	t<10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-11.1 -8.9	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	-60	А
Continuous Source-Drain Diode Current (Note 6)	T <sub>A</sub> = +25°C	ls	-2.4	А	
Avalanche Current (Note 7) L = 0.1mH		I <sub>AS</sub>	-27	А	
Avalanche Energy (Note 7) L = 0.1mH	E <sub>AS</sub>	38	mJ		

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Dower Dissinction (Note 5)	T <sub>A</sub> = +25°C	D	0.73	W	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	PD	0.47		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	P	172	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ extsf{ heta}}JA$	121		
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	Р	2.02	W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	PD	1.30		
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	63	°C/W	
Thermal Resistance, Junction to Amblent (Note 6)	t<10s	$R_{ extsf{ heta}JA}$	42		
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	18		
Operating and Storage Temperature Range		T <sub>J.</sub> T <sub>STG</sub>	-55 to +150	°C	

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

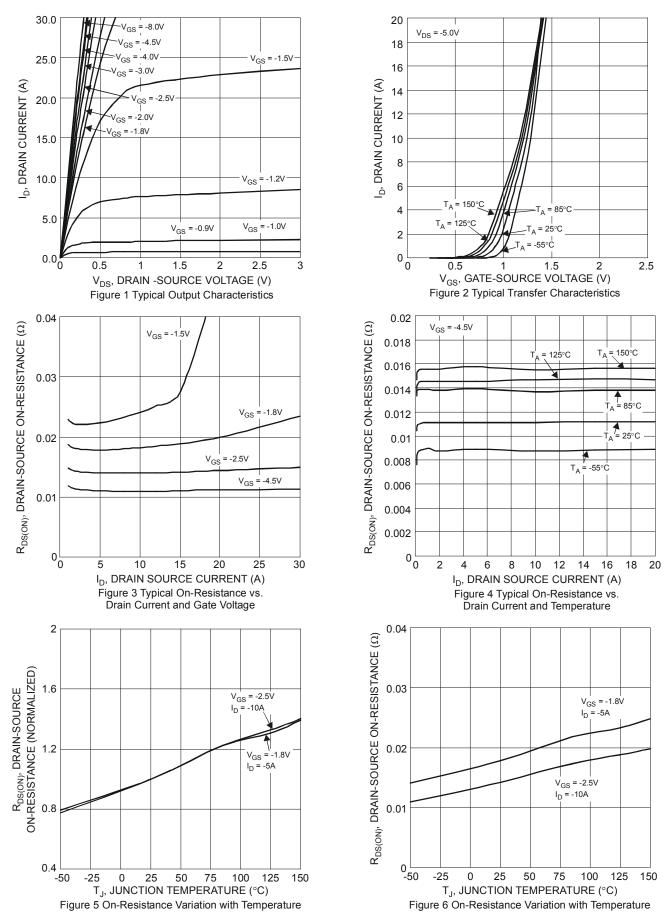
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	Cymbol	WIIII	TYP	Max	Onit	rest condition
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current $T_J$ = +25°C	IDSS		_	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>		_	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)	000					
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.35	_	-1.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
			12	16		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -7.0A
Static Drain-Source On-Resistance			15	22	mΩ	V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -5.0A
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	19	40	mΩ	V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -3.0A
			21	80		V <sub>GS</sub> = -1.5V, I <sub>D</sub> = -1.0A
Diode Forward Voltage	V <sub>SD</sub>		-0.8	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.0A
DYNAMIC CHARACTERISTICS (Note 9)			•			•
Input Capacitance	Ciss	_	2,760	—		
Output Capacitance	Coss	_	262	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	220	—		1 - 1.0MHz
Gate Resistance	Rg		16	30	Ω	$V_{DS}$ = 0V, $V_{GS}$ = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg		34	—		
Total Gate Charge (V <sub>GS</sub> = -8V)	Qg		59	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	_	3.5	—	nc	$V_{DS}$ = -15V, $I_{D}$ = -4.0A
Gate-Drain Charge	Q <sub>gd</sub>		8.3	—		
Turn-On Delay Time	t <sub>D(on)</sub>	_	7.5	—		
Turn-On Rise Time	tr		25	—		V <sub>DS</sub> = -15V, V <sub>GS</sub> = -4.5V,
Turn-Off Delay Time	t <sub>D(off)</sub>	_	125	—	ns	$R_{\rm G} = 1\Omega, I_{\rm D} = -4.0A$
Turn-Off Fall Time	t <sub>f</sub>	_	96	—		
Reverse Recovery Time	t <sub>rr</sub>	_	48	_	ns	I <sub>F</sub> = -1.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>rr</sub>		33	_	nC	I <sub>F</sub> = -1.0A, di/dt = 100A/µs

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. 7.  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ . Notes:

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

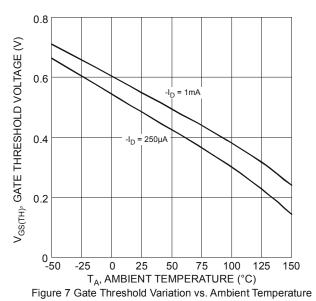


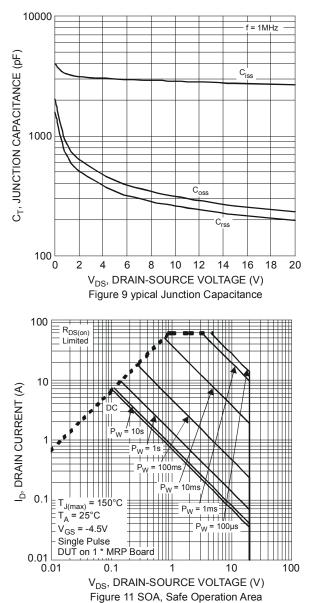


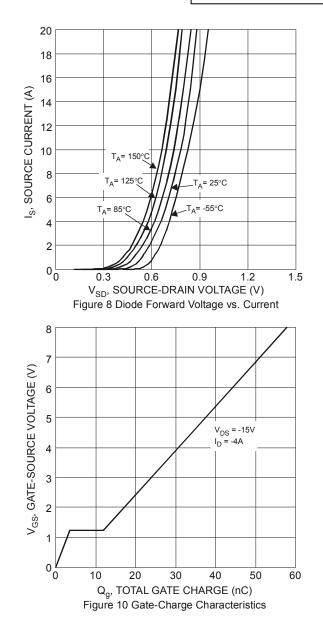
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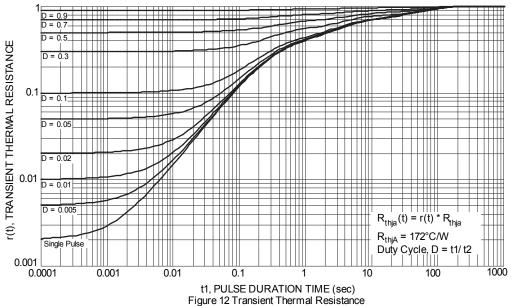








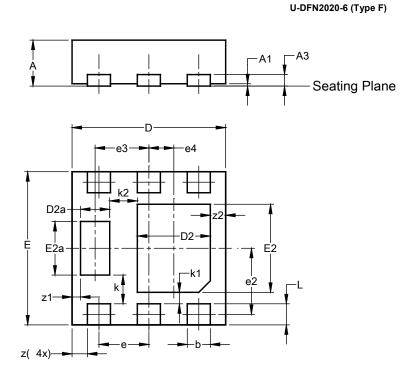






## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

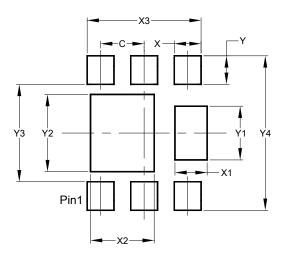


	U-DFN2020-6 (Type F)						
Dim	Min	Max	Тур				
Α	0.57	0.57 0.63 0.60					
A1	0.00	0.05	0.03				
A3	1	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.33 0.43 0					
E	1.95 2.05 2.0						
E2	1.05 1.25 1.1						
E2a	0.65	0.75	0.70				
е		0.65 BS	С				
e2	C	).863 BS	SC				
e3		0.70 BS	-				
e4	C	).325 BS	SC				
k		0.37 BS	С				
k1		0.15 BS	С				
k2		0.36 BS	С				
L		0.325					
z	0.20 BSC						
z1	0.110 BSC						
z2		0.20 BS	С				
All D	imens	ions in	mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value
Dimensions	(in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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